

ABSTRACT

A method for manufacturing an electronic device, the method at least including a step (A) of preparing a structure which includes a wafer including a circuit forming surface, and an adhesive film bonded to the circuit forming surface side of the wafer, a step (B) of back-grinding a surface of the wafer on a side opposite to the circuit forming surface side; and a step (C) of removing the adhesive film from the wafer after the adhesive film is irradiated with an ultraviolet ray. This adhesive film includes a base material layer, and an adhesive resin layer which is provided on one surface side of the base material layer and configured with an ultraviolet curable adhesive resin material. In the step (C), regarding the adhesive resin layer of the adhesive film after being irradiated with an ultraviolet ray, a storage elastic modulus at 100°C measured under the following conditions, defined as $E' (100^{\circ}\text{C})$, is 1.0×10^6 to 3.5×10^7 Pa, and $E' (100^{\circ}\text{C})/E' (-15^{\circ}\text{C})$ is 2.0×10^{-3} to 1.5×10^{-2} . (Conditions) A dynamic viscoelasticity is measured at a frequency of 1 Hz and a temperature of -50°C to 200°C in a tensile mode.